



Technical Data : CD-019

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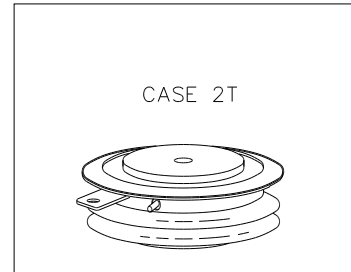
POSITIONING PSTC430 - Power Thyristor

500 - 1400 V_{DRM}; 1000 A rms

HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS

Features:

- . All Diffused Structure
- . Center Amplifying Gate Configuration
- . Blocking capability up to 1400 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V _{RRM} (1)	V _{DRM} (1)	V _{RSM} (1)
PSTC430E	500	500	600
PSTC430M	600	600	720
PSTC430N	800	800	960
PSTC430P	1000	1000	1150
PSTC430PB	1200	1200	1300
PSTC430PD	1400	1400	1500

V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I _{RRM} / I _{DRM}	15 mA 30 mA (3)
Critical rate of voltage rise (4)	dV/dt	200 V/μsec

Notes:

All ratings are specified for T_j=25 °C unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to +125 °C.

(2) 10 msec. max. pulse width

(3) Maximum value for T_j = 125 °C.

(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM}. Gate open. T_j = 125 °C.

(5) Non-repetitive value.

(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thyristor under test.

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	I _{T(AV)}		700		A	Sinewave, 180° conduction, T _c = 65°C
RMS value of on-state current	I _{TRMS}		1000		A	Nominal value
Peak one cPSTCLe surge (non repetitive) current	I _{TSM}		8000 7400		A A	8.3 msec (60Hz), sinusoidal wave-shape, 180° conduction, T _j = 125 °C 10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j = 125 °C
I square t	I ² t		265000		A ² s	8.3 msec and 10.0 msec
Latching current	I _L		800		mA	V _D = 24 V; R _L = 12 ohms
Holding current	I _H		400		mA	V _D = 24 V; I = 2.5 A
Peak on-state voltage	V _{TM}		2.20		V	I _{TM} = 2000 A; Duty cPSTCLe ≤ 0.01%
Critical rate of rise of on-state current (5, 6)	di/dt		400		A/μs	Switching from V _{DRM} ≤ 1000 V, non-repetitive
Critical rate of rise of on-state current (6)	di/dt		150		A/μs	Switching from V _{DRM} ≤ 1000 V

ELECTRICAL CHARACTERISTICS AND RATINGS (cont'd)

PSTC430 - Power

Thyristor

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		200		W	$t_p = 40 \mu s$
Average gate power dissipation	$P_{G(AV)}$		5		W	
Peak gate current	I_{GM}		10		A	
Gate current required to trigger all units	I_{GT}		300 150 125		mA mA mA	$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +25^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +125^\circ C$
Gate voltage required to trigger all units	V_{GT}	0.15	5 3		V V V	$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = 0-125^\circ C$ $V_D = \text{Rated } V_{DRM}; R_L = 1000 \text{ ohms}; T_j = +125^\circ C$
Peak negative voltage	V_{GRM}		5		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d		1.5	0.7	μs	$I_{TM} = 50 A; V_D = \text{Rated } V_{DRM}$ Gate pulse: $V_G = 20 V; R_G = 20 \text{ ohms}; t_r = 0.1 \mu s; t_p = 20 \mu s$
Turn-off time (with $V_R = -50 V$)	t_q		200	125	μs	$I_{TM} = 500 A; di/dt = 25 A/\mu s;$ $V_R \geq -50 V; \text{Re-applied } dV/dt = 20 V/\mu s \text{ linear to } 80\% V_{DRM}; V_G = 0;$ $T_j = 125^\circ C; \text{Duty cPSTC} \geq 0.01\%$
Reverse recovery charge	Q_{rr}		*		μC	$I_{TM} = 500 A; di/dt = 25 A/\mu s;$ $V_R \geq -50 V$

* For guaranteed max. value, contact factory.

THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

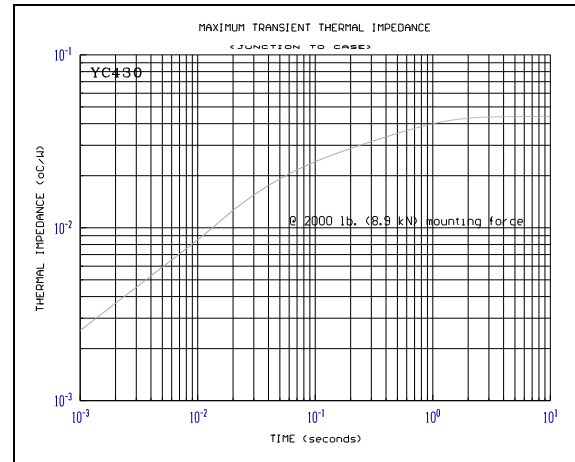
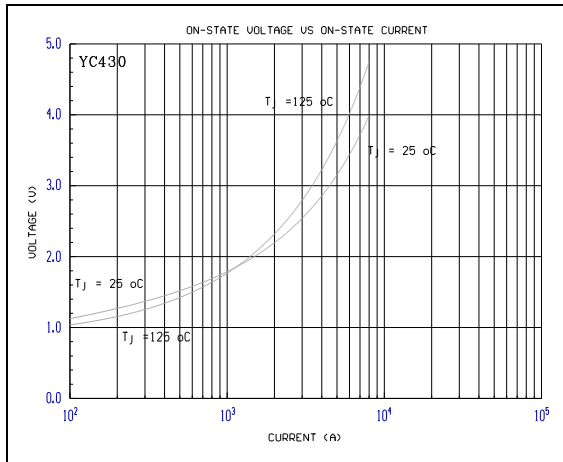
Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+125		$^\circ C$	
Storage temperature	T_{stg}	-40	+150		$^\circ C$	
Thermal resistance - junction to case	$R_{\theta(j-c)}$	0.045 (1)	0.055 (2)		$^\circ C/W$	Double sided cooled * (1) @ 2000 lb.; (2) @ 800 lb.
Thermal resistance - junction to case	$R_{\theta(j-c)}$	0.090 (1)	0.110 (2)		$^\circ C/W$	Single sided cooled * (1) @ 2000 lb.; (2) @ 800 lb.
Thermal resistance - case to sink	$R_{\theta(c-s)}$		.030 .060		$^\circ C/W$	Double sided cooled * Single sided cooled *
Mounting force	P	800 3.6	2500 11.1		lb. kN	
Weight	W			2.5 70	oz. g	

* Mounting surfaces smooth, flat and greased

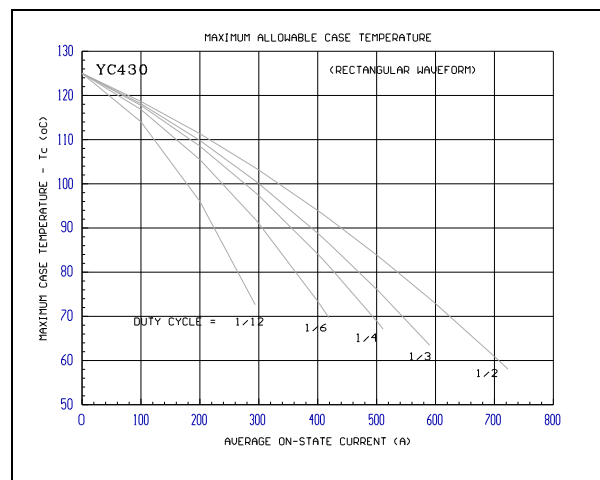
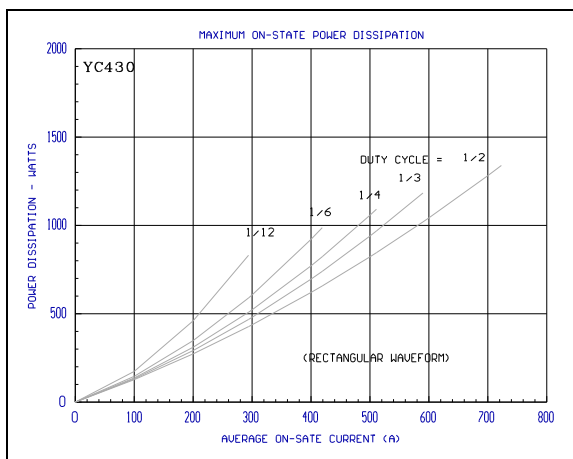
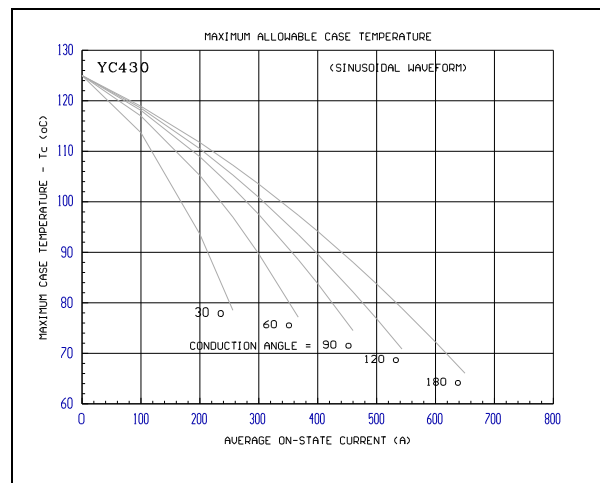
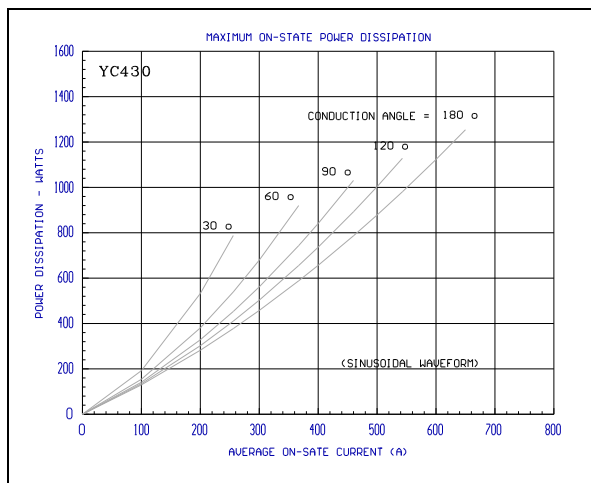
Note : for case outline and dimensions, see case outline drawing in page 4 of this Technical Data

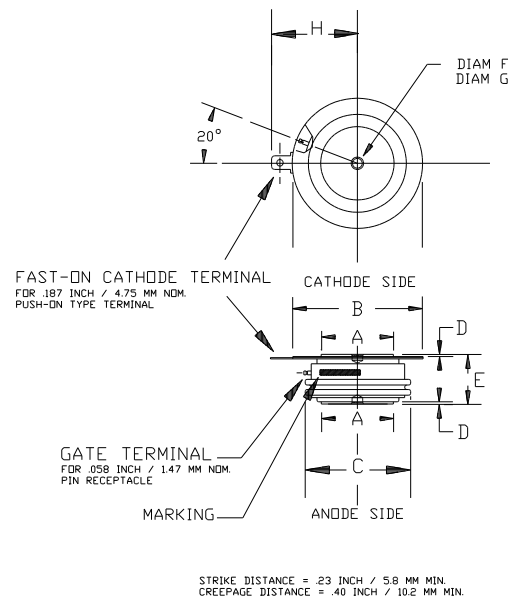
ELECTRICAL CHARACTERISTICS AND RATINGS (cont'd)

PSTC430 - Power



Thyristor





OUTLINE DIMENSIONS - CASE 2T				
DIMENSIONS	Min. mm	Max. mm	Min. In.	Max. In.
DIAM A	24.89	25.40	0.98	1.00
DIAM B	40.64	42.16	1.60	1.65
DIAM C	--	40.39	--	1.59
D	0.76	--	0.03	--
E	13.72	15.24	0.54	0.60
F	3.30	3.81	0.13	0.15
G	1.78	2.03	0.07	0.08
H	27.69	28.70	1.09	1.13

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